EVVOSEMI®
THINK CHANGE DO

ESD TVS MOS LDO Diode Sensor DC-DC

Product Specification

Domestic Part Number	IRFB4620
Overseas Part Number	IRFB4620
Equivalent Part Number	IRFB4620

200V N-Channel Enhancement Mode MOSFET

Description

The IRFB4620 is silicon N-channel Enhanced VDMOSFETs, is obtained by the self-aligned planar Technology which reduce the conduction loss, improve switching performance and enhance the avalanche energy. The transistor can be used in various power switching circuit for system miniaturization and higher efficiency.

Product Summary

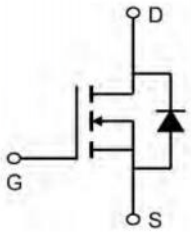
VDS =200V,ID =60A

RDS(ON) <50mΩ@ VGS=10V

Application

Power amplifier

Pin Configuration



TO-220-3L

TO-252-2L

Absolute Maximum Ratings

Symbol	Parameter	Value	Unit
VDSS	Drain-Source Voltage	200	V
ID	Drain Current -continuous	60	A
IDM	Drain Current -pulse	120	A
VGSS	Gate-Source Voltage	±30	V
EAS	Single Pulsed Avalanche Energy	588	mJ
IAR	Avalanche Current	40	A
EAR	Repetitive Avalanche Current	15.8	mJ
dv/dt	Peak Diode Recovery dv/dt	5.5	V/ns
PD TC=25℃	Power Dissipation	158	W
TJ，TSTG	Operating and Storage Temperature Range	-55～+150	℃
TL	Maximum Lead Temperature for Soldering Purposes	300	℃
Rth(j-c)	Thermal Resistance, Junction to Case	0.79	℃/W
Rth(j-A)	Thermal Resistance, Junction to Ambient	62.5	℃/W

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Electrical Characteristics (TJ=25℃ unless otherwise specified)

Symbol	Parameter	Tests conditions	Min	Typ	Max	Units
BV_{DSS}	Drain-Source Voltage	I_D=250μA, V_{GS}=0V	200	-	-	V
ΔBVDSS /ΔTJ	Breakdown Voltage Temperature Coefficient	I_D=250μA, referenced to 25℃	-	0.19	-	V/℃
IDSS	Zero Gate Voltage Drain Current	V_{DS}=200V, V_{GS}=0V, T_C=25℃	-	-	1	μA
IGSSF	Gate-body leakage current, forward	V_{DS}=0V, V_{GS} =30V	-	-	100	nA
IGSSR	Gate-body leakage current, reverse	V_{DS}=0V, V_{GS} =-30V	-	-	-100	nA
VGS(th)	Gate Threshold Voltage	V_{DS} = V_{GS} , I_D=250μA	2.0	-	4.0	V
RDS(ON)	Static Drain-Source On-Resistance	V_{GS} =10V , I_D=14.0A	-	32	50	mΩ
g_{fs}	Forward Transconductance	V_{DS} = 40V , I_D=14.0A	-	24	-	S
C_{iss}	Input capacitance	V_{DS}=25V, V_{GS} =0V, f=1.0MHz	-	2879	3742	pF
C_{oss}	Output capacitance		-	362	470	pF
C_{rss}	Reverse transfer capacitance		-	81	105	pF
t_d(on)	Turn-On delay time	V_{DD}=100V,I_D=28A,R_G=25Ω V_{GS} =10V （note 4，5）	-	28	69	ns
t_r	Turn-On rise time		-	251	494	ns
t_d(off)	Turn-Off delay time		-	309	617	ns
t_f	Turn-Off Fall time		-	220	412	ns
Q_g	Total Gate Charge	V_{DS} =160V , I_D=28A V_{GS} =10V（note 4，5）	-	103	136	nC
Q_{gs}	Gate-Source charge		-	16	-	nC
Q_{gd}	Gate-Drain charge		-	53	-	nC
IS	Maximum Continuous Drain-Source Diode Forward Current		-	-	28	A
ISM	Maximum Pulsed Drain-Source Diode Forward Current		-	-	112	A
VSD	Maximum Continuous Drain-Source Diode Forward Current	V_{GS}=0V, I_S=28A	-		1.4	V
trr	Reverse recovery time	V_{GS}=0V, I_S=28A dI_F/dt=100A/μs (note 4)		218		ns
Q_{rr}	Reverse recovery charge			1.91		μC

Notes:

1: Pulse width limited by maximum junction temperature

2: L=1.5mH, I_{AS}=28A, V_{DD}=50V, R_G=25 Ω,Starting T_J=25℃

3: I_{SD} ≤28A,di/dt ≤200A/μs, VDD≤BV_{DSS}, Starting T_J=25℃

4: Pulse Test: Pulse Width ≤300μs, Duty Cycle≤2%

5: Essentially independent of operating temperature

Electrical Characteristics Diagrams

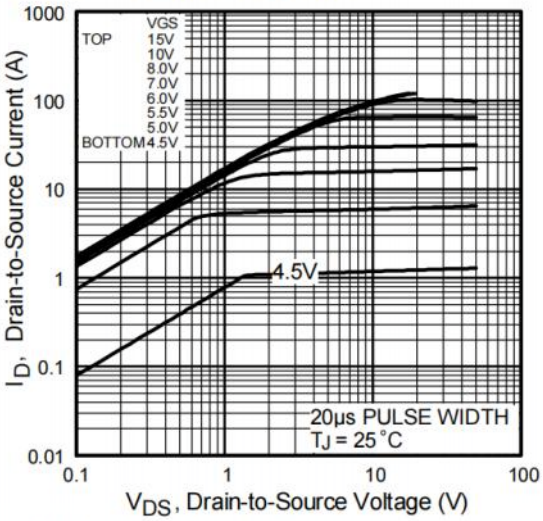


Fig 1. Typical Output Characteristics

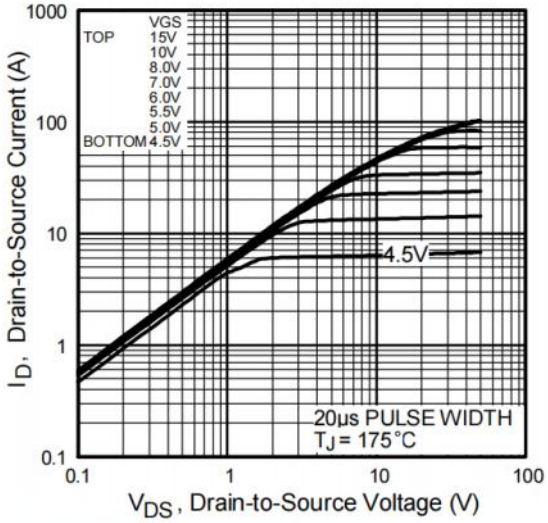


Fig 2. Typical Output Characteristics

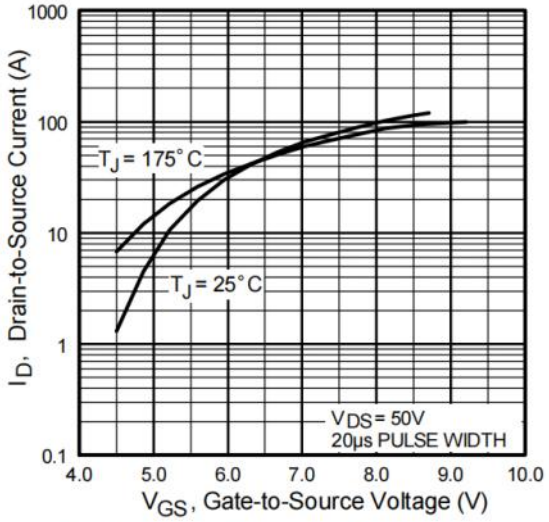


Fig 3. Typical Transfer Characteristics

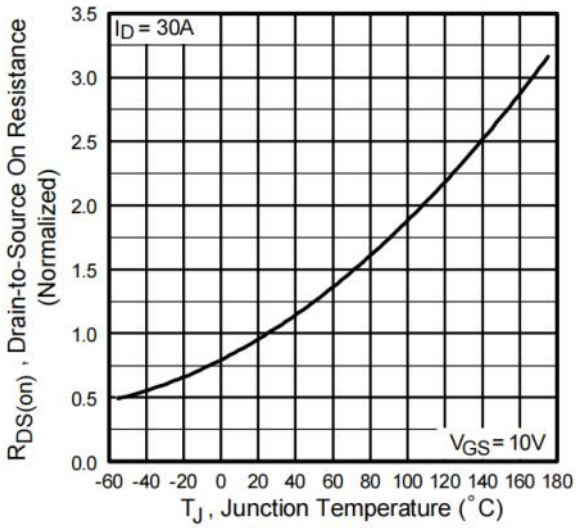


Fig 4. Normalized On-Resistance Vs. Temperature

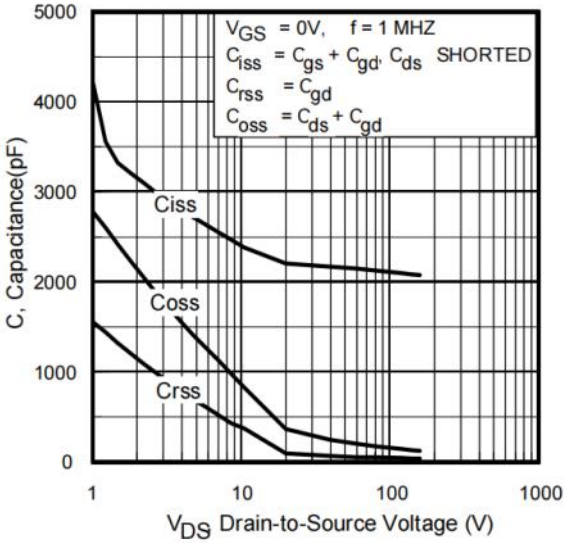


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

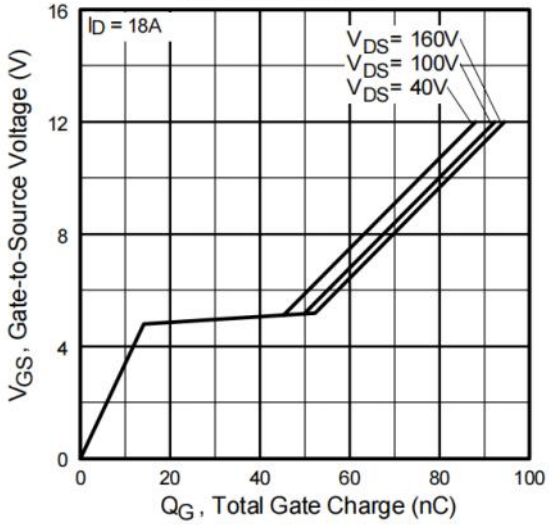
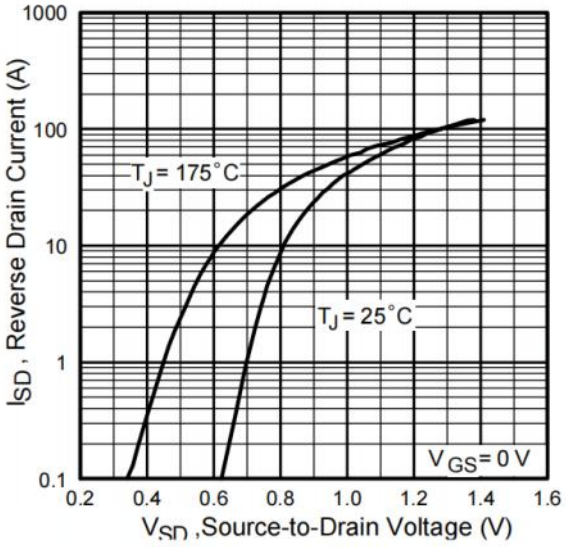


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage



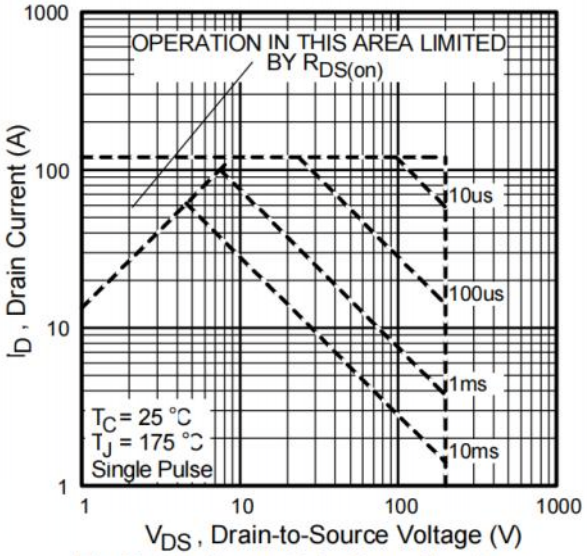


Fig 8. Maximum Safe Operating Area

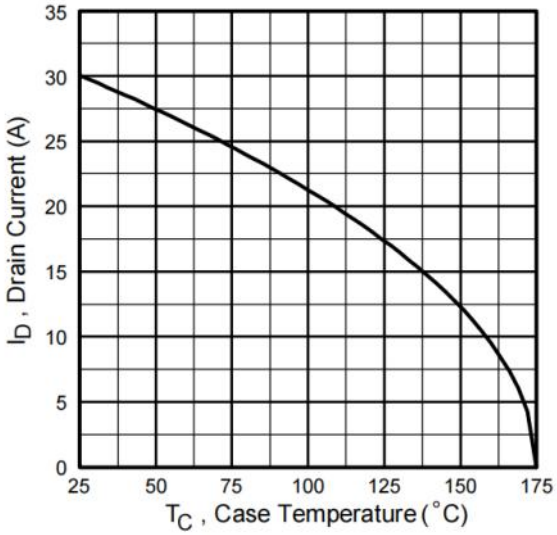


Fig 9. Maximum Drain Current Vs. Case Temperature

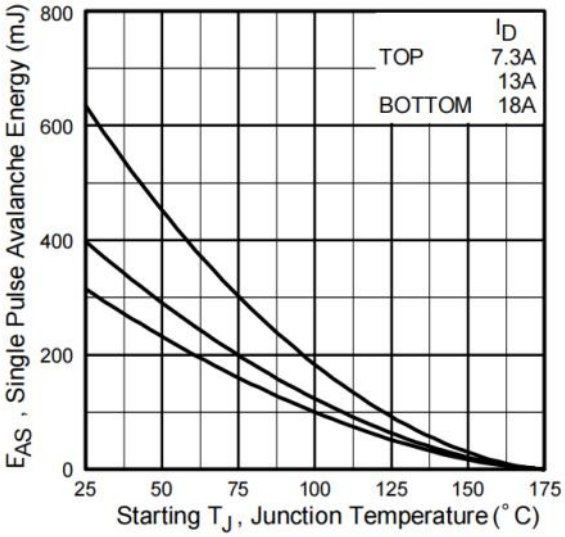


Fig 12c. Maximum Avalanche Energy Vs. Drain Current

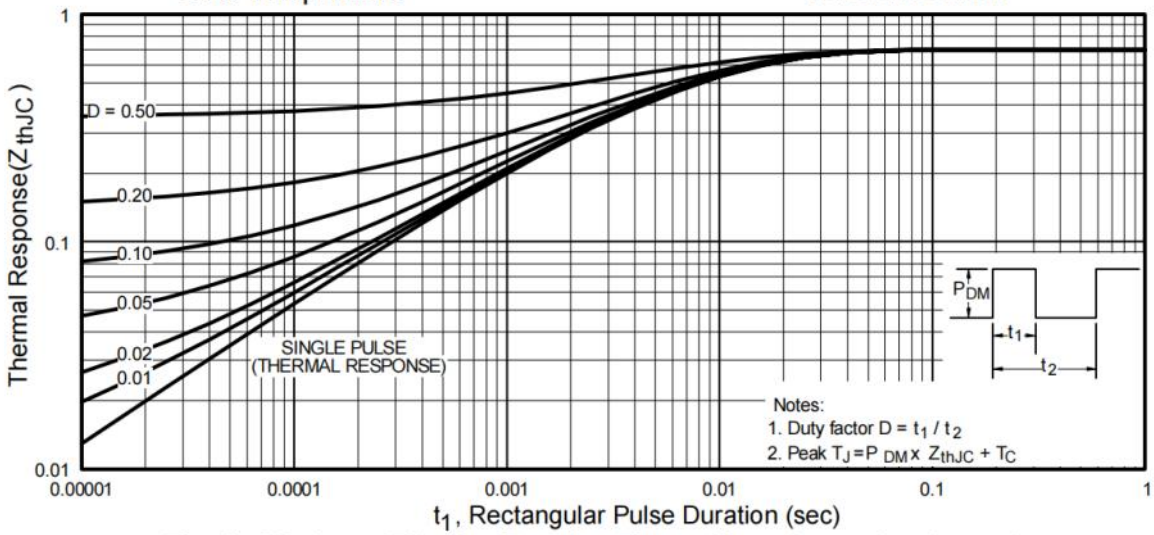


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

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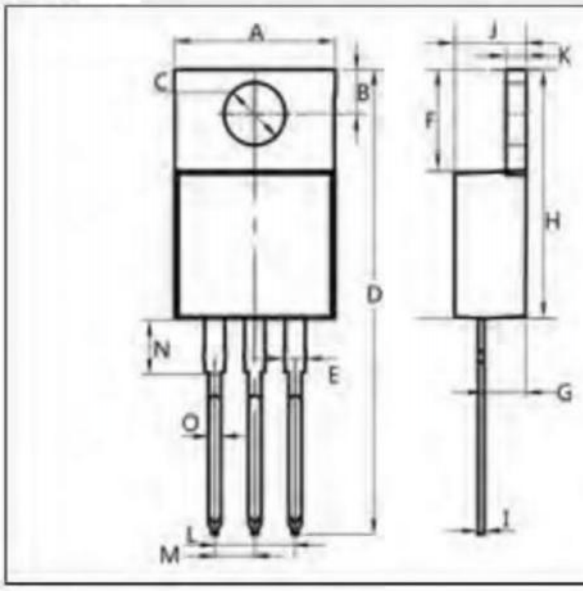
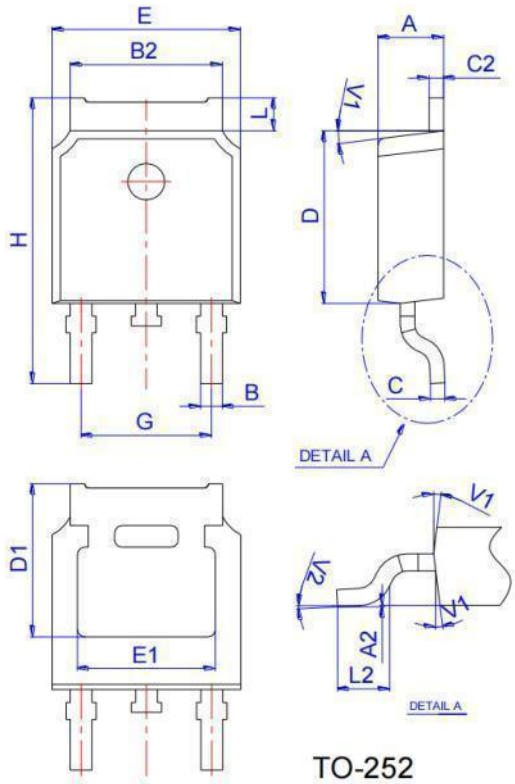


Dim.	Min.	Max.
A	10.0	10.4
B	2.5	3.0
C	3.5	4.0
D	28.0	30.0
E	1.1	1.5
F	6.2	6.6
G	2.9	3.3
H	15.0	16.0
I	0.35	0.45
J	4.3	4.7
K	1.2	1.4
L	Typ 5.08	
M	Typ 2.54	
N	3.1	3.5
O	0.7	0.9
All Dimensions in millimeter		

TO-252-2L



TO-252

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.10		2.50	0.083		0.098
A2	0		0.10	0		0.004
B	0.66		0.86	0.026		0.034
B2	5.18		5.48	0.202		0.216
C	0.40		0.60	0.016		0.024
C2	0.44		0.58	0.017		0.023
D	5.90		6.30	0.232		0.248
D1	5.30REF			0.209REF		
E	6.40		6.80	0.252		0.268
E1	4.63			0.182		
G	4.47		4.67	0.176		0.184
H	9.50		10.70	0.374		0.421
L	1.09		1.21	0.043		0.048
L2	1.35		1.65	0.053		0.065
V1		7°			7°	
V2	0°		6°	0°		6°

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